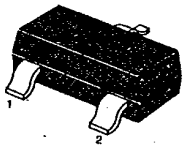
MMBTA70 PNP EPITAXIAL SILICON TRANSISTOR

AMPLIFIER TRANSISTOR

SOT-23



1. Base 2. Emitter 3. Collector

ABSOLUTE MAXIMUM RATINGS (T_a=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	4	V
Collector Current	I_C	100	mA
Collector Dissipation	P_C	350	mW
Storage Temperature	Tstg	150	°C

• Refer to MMBT5086 for graphs

ELECTRICAL CHARACTERISTICS (T_a=25°C)

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector-Emitter Breakdown Voltage	BV_{CEO}	I_C=1.0mA, I_B=0	40		V
Emitter-Base Breakdown Voltage	BV_{EBO}	I_E=100μA, I_C=0	4		V
Collector Cutoff Current	I_{CBO}	V_{CB}=30V, I_E=0		100	nA
DC Current Gain	h_{FE}	V_{CE}=10V, I_C=5.0mA	40	400	
Collector-Emitter Saturation Voltage	V_{CE} (sat)	I_C=10mA, I_B=1.0mA		0.25	V
Current Gain-Bandwidth Product	f_T	I_C=5.0mA, V_{CE}=10V f=100MHz	125		MHz
Output Capacitance	Cob	V_{CB}=10V, I_E=0 f=100KHz		4.0	pF

3

Marking